

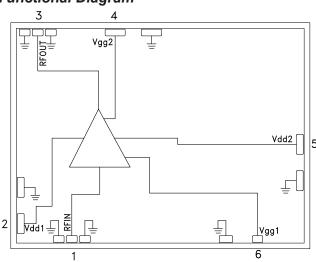


#### Typical Applications

The HMC7149 is ideal for:

- Test Instrumentation
- General Communications
- Radar

#### **Functional Diagram**



#### **Features**

High Psat: +40 dBm

Power Gain at Psat: +10 dB
High Output IP3: +39.5 dBm
Small Signal Gain: 20 dB

Supply Voltage: +28 V @ 680 mA 50 Ohm Matched Input/Output Die Size: 3.4 x 4.5 x 0.1 mm

#### **General Description**

The HMC7149 is an 10W Gallium Nitride (GaN) MMIC Power Amplifier which operates between 6 and 18 GHz. The amplifier typically provides 20dB of small signal gain, +40 dBm of saturated output power, and +39.5 dBm output IP3 at +28 dBm output power per tone. The HMC7149 draws 680 mA current from a +28V DC supply. The RF I/Os are matched to 50 Ohms for ease of integration into Multi-Chip-Modules (MCMs). All electrical performance data was aquired with the die eutectically attached to 1.02 mm (40 mil) thick CuMo carrier with multiple 1.0 mil diameter ball bonds connecting the die to 50 Ohm transmission lines on alumina.

Electrical Specifications, Tc = +25°C, Vdd= Vdd1 = Vdd2 = +28 V, Idd = 680 mA [1]

Parameter	Min.	Тур.	Max.	Min.	Тур.	Max.	Min.	Тур.	Max.	Min.	Тур.	Max.	Units
Frequency Range		6 - 10			10 - 14			14 - 16			16 - 18		GHz
Small Signal Gain	19	21		18	20		17	19		18	20		dB
Gain Flatness		±0.5			±0.6			±0.5			±0.7		dB
Gain Variation Over Temperature		0.023			0.02			0.02			0.018		dB/ °C
Input Return Loss		17			17			16			11		dB
Output Return Loss		17			17			18			12		dB
Output Power for 4 dB Compression (P4dB)		35			35			35			36		dBm
Power Gain for 4 dB compression (P4dB)		17			16			15			17		dB
Saturated Output Power (Psat)		40			40			40			40		dBm
Output Third Order Intercept (IP3) [2]		39.5			39			39.5			40.5		dBm
Power Added Efficiency		22			20			20			20		%
Supply Current (Idd @ Vdd = 28V)		680			680			680			680		mA

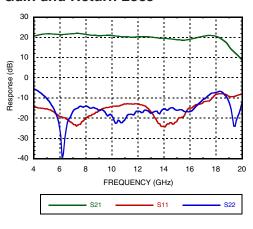
<sup>[1]</sup> Adjust Vgg between -3V and 0V to achieve Idd= 680 mA typical.

<sup>[2]</sup> Measurement taken at 28V @ 680 mA, Pout/tone = +28 dBm.

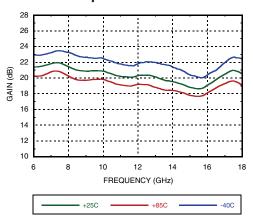




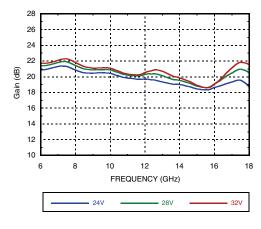
#### Gain and Return Loss



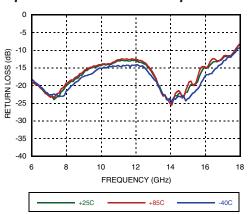
#### Gain vs. Temperature



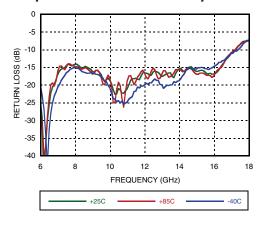
#### Gain vs. Vdd



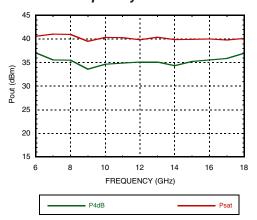
#### Input Return Loss vs. Temperature



#### Output Return Loss vs. Temperature



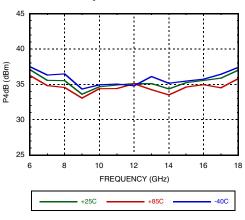
#### Pout vs. Frequency



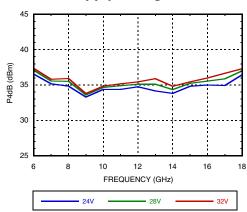




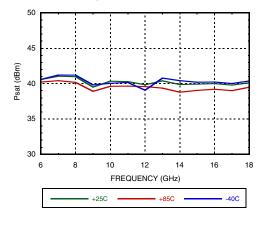
#### P4dB vs. Temperature



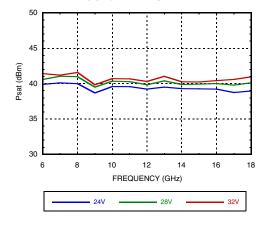
### P4dB vs. Supply Voltage



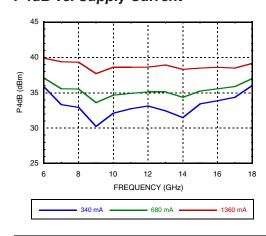
#### Psat vs. Temperature



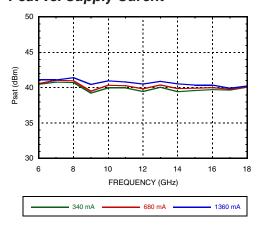
Psat vs. Supply Voltage



#### P4dB vs. Supply Current



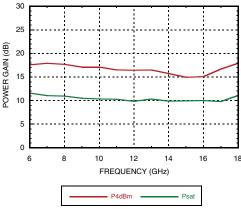
#### Psat vs. Supply Curent





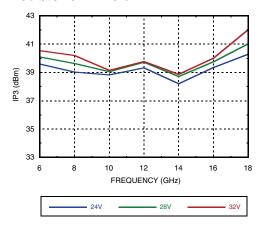


#### Power Gain vs. Frequency

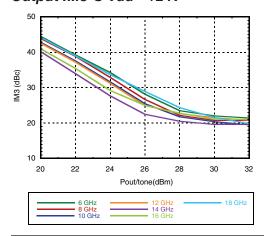


# Output IP3 vs. Supply Voltage

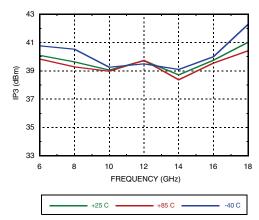
Pout/tone = +28 dBm



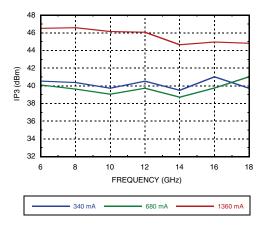
#### Output IM3 @ Vdd= +24V



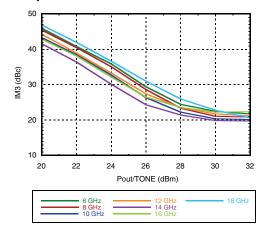
#### Output IP3 vs. Temperature Pout/tone = +28 dBm



#### **Output IP3 vs. Supply Current** Pout/tone = +28 dBm



#### Output IM3 @ Vdd= +28V



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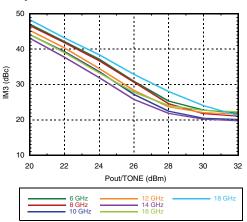




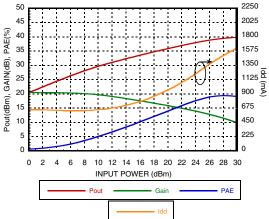
# 10 WATT Gan MMIC POWER AMPLIFIER,

6 - 18 GHz

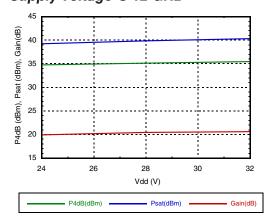
#### Output IM3 @ Vdd= +32V



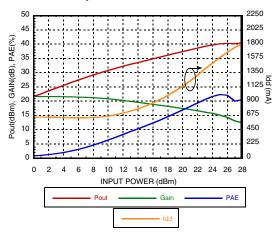
#### **Power Compression @ 12 GHz**



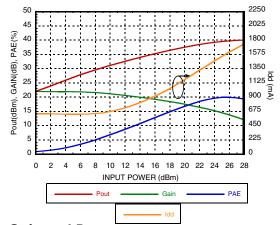
# Gain and Power vs. Supply Voltage @ 12 GHz



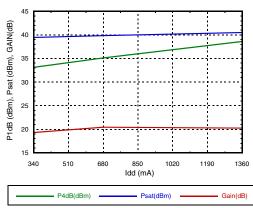
#### Power Compression @ 6 GHz



#### **Power Compression @ 18 GHz**



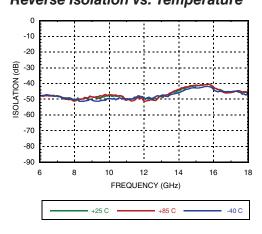
# Gain and Power vs. Supply Curent @ 12 GHz



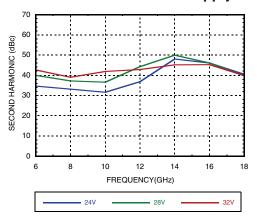




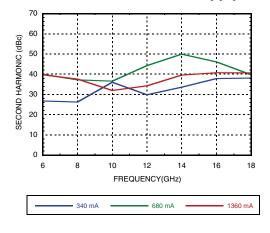
# Reverse Isolation vs. Temperature



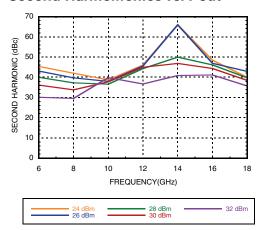
#### Second Harmomonics vs. Supply Voltage



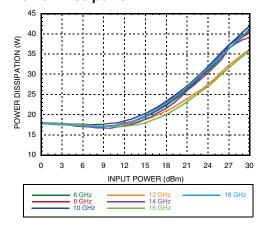
#### Second Harmomonics vs. Supply Current



#### Second Harmomonics vs. Pout



#### **Power Dissipation**







#### Absolute Maximum Ratings[1]

Drain Bias Voltage (Vdd)	+32V
Gate Bias Voltage (Vgg)	-8V to +0V
Maximum Forward Gate Current	6 mA
Maximum RF Input Power (RFIN)	30 dBm
Maximum Junction Temperature (Tj)	225 °C
Maximum Pdiss (T=85°C) (Derate 357 mW/°C above 85°C)	50 W
Thermal Resistance [2]	2.8 °C/W
Maximum VSWR [3]	6:1
Storage Temperature	-55 to +150 °C
Operating Temperature	-40 to +85 °C

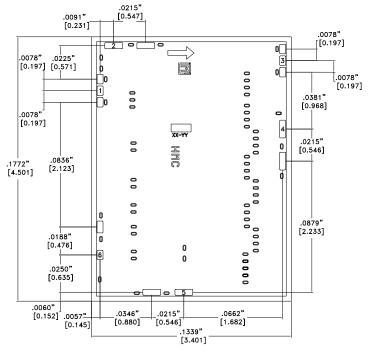
#### Typical Supply Current vs. Vdd

Vdd (V)	Idd (mA)
+28.0	680



<sup>[1]</sup> Operation outside parameter ranges above can cause permanent damage to the device. These are maximum stress ratings only. Continuous operation of the device at these conditions is not implied.

#### **Outline Drawing**



#### Die Packaging Information [1]

Standard	Alternate		
GP-1 (Gel Pack)	[2]		

[1] Refer to the "Packaging Information" section for die packaging dimensions.

[2] For alternate packaging information contact Hittite Microwave Corporation.

- 1. ALL DIMENSIONS ARE IN INCHES [MM]
- 2. DIE THICKNESS IS .004"
- 3. TYPICAL BOND PAD IS .004" SQUARE
- 4. BACKSIDE METALLIZATION: GOLD
- 5. BOND PAD METALLIZATION: GOLD
- 6. BACKSIDE METAL IS GROUND.
- 7. CONNECTION NOT REQUIRED FOR UNLABELED BOND PADS.
- 8. OVERALL DIE SIZE ± .002

<sup>[2]</sup> Assumes 1mil AuSn die attach to a 40mil CuMo Carrier with 85°C at the back of the carrier.

<sup>[3]</sup> Restricted by maximum power dissipation





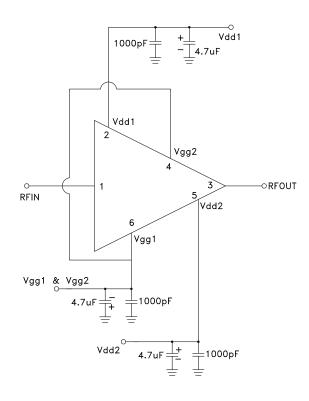
#### **Pad Descriptions**

Pad Number	Function	Description	Interface Schematic
1	RFIN	This pad is AC coupled and is matched to 50 Ohms. External blocking capacitor is required.	RFINO USAN STATE OF THE STATE O
2	Vdd1	Drain Bias	Vdd1
3	RFOUT	This pad is DC coupled and is matched to 50 Ohms. External blocking capacitor is required.	RFOUT Vdd2
4	Vgg2	Gate Bias	Vdd10-
5	Vdd2	Drain Bias	RFOUT Vdd2
6	Vgg1	Gate Bias	RFINO E
Die Bottom	GND	Die bottom must be connected to RF/DC ground.	○ GND =





### **Application Circuit**



#### **Assembly Diagram**

